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What is "[Embedded - Microcontrollers](#)"?

"[Embedded - Microcontrollers](#)" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "[Embedded - Microcontrollers](#)"

Details

Product Status	Discontinued at Digi-Key
Core Processor	RL78
Core Size	16-Bit
Speed	32MHz
Connectivity	CSI, I ² C, LINbus, UART/USART
Peripherals	DMA, LVD, POR, PWM, WDT
Number of I/O	21
Program Memory Size	128KB (128K x 8)
Program Memory Type	FLASH
EEPROM Size	8K x 8
RAM Size	12K x 8
Voltage - Supply (Vcc/Vdd)	1.6V ~ 5.5V
Data Converters	A/D 8x8/10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	30-LSSOP (0.240", 6.10mm Width)
Supplier Device Package	30-LSSOP
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f100agdsp-x0

Table 1-1. List of Ordering Part Numbers

(1/12)

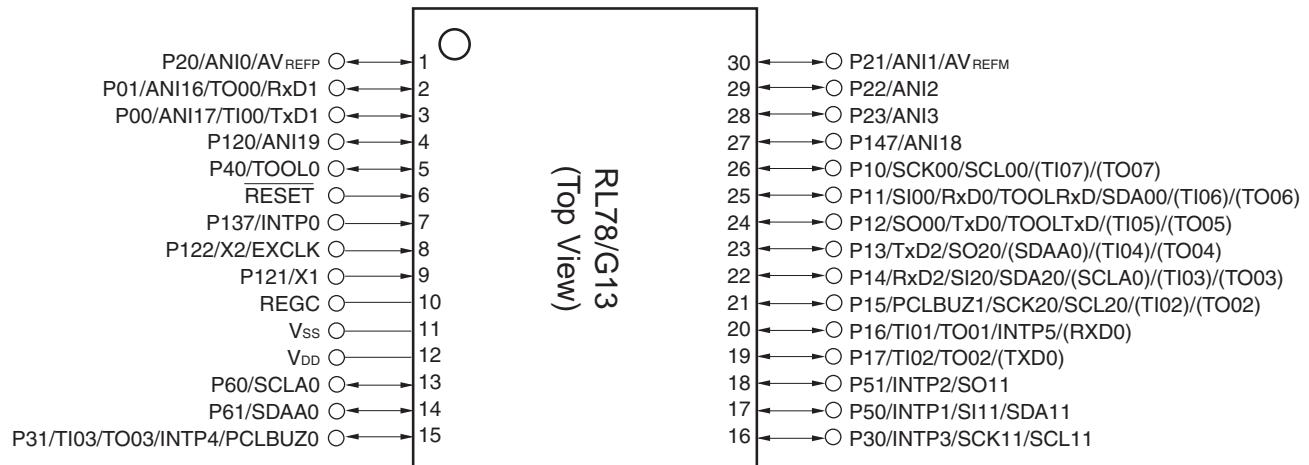
Pin count	Package	Data flash	Fields of Application ^{Note}	Ordering Part Number
20 pins	20-pin plastic LSSOP (7.62 mm (300), 0.65 mm pitch)	Mounted	A	R5F1006AASP#V0, R5F1006CASP#V0, R5F1006DASP#V0, R5F1006EASP#V0 R5F1006AASP#X0, R5F1006CASP#X0, R5F1006DASP#X0, R5F1006EASP#X0
			D	R5F1006ADSP#V0, R5F1006CDSP#V0, R5F1006DDSP#V0, R5F1006EDSP#V0 R5F1006ADSP#X0, R5F1006CDSP#X0, R5F1006DDSP#X0, R5F1006EDSP#X0
			G	R5F1006AGSP#V0, R5F1006CGSP#V0, R5F1006DGSP#V0, R5F1006EGSP#V0 R5F1006AGSP#X0, R5F1006CGSP#X0, R5F1006DGSP#X0, R5F1006EGSP#X0
		Not mounted	A	R5F1016AASP#V0, R5F1016CASP#V0, R5F1016DASP#V0, R5F1016EASP#V0 R5F1016AASP#X0, R5F1016CASP#X0, R5F1016DASP#X0, R5F1016EASP#X0
			D	R5F1016ADSP#V0, R5F1016CDSP#V0, R5F1016DDSP#V0, R5F1016EDSP#V0 R5F1016ADSP#X0, R5F1016CDSP#X0, R5F1016DDSP#X0, R5F1016EDSP#X0
			A	R5F1007AANA#U0, R5F1007CANA#U0, R5F1007DANA#U0, R5F1007EANA#U0 R5F1007AANA#W0, R5F1007CANA#W0, R5F1007DANA#W0, R5F1007EANA#W0
			D	R5F1007ADNA#U0, R5F1007CDNA#U0, R5F1007DDNA#U0, R5F1007EDNA#U0 R5F1007ADNA#W0, R5F1007CDNA#W0, R5F1007DDNA#W0, R5F1007EDNA#W0
			G	R5F1007AGNA#U0, R5F1007CGNA#U0, R5F1007DGNA#U0, R5F1007EGNA#U0 R5F1007AGNA#W0, R5F1007CGNA#W0, R5F1007DGNA#W0, R5F1007EGNA#W0
		Not mounted	A	R5F1017AANA#U0, R5F1017CANA#U0, R5F1017DANA#U0, R5F1017EANA#U0 R5F1017AANA#W0, R5F1017CANA#W0, R5F1017DANA#W0, R5F1017EANA#W0
			D	R5F1017ADNA#U0, R5F1017CDNA#U0, R5F1017DDNA#U0, R5F1017EDNA#U0 R5F1017ADNA#W0, R5F1017CDNA#W0, R5F1017DDNA#W0, R5F1017EDNA#W0

Note For the fields of application, refer to **Figure 1-1 Part Number, Memory Size, and Package of RL78/G13**.

Caution The ordering part numbers represent the numbers at the time of publication. For the latest ordering part numbers, refer to the target product page of the Renesas Electronics website.

1.3.4 30-pin products

- 30-pin plastic LSSOP (7.62 mm (300), 0.65 mm pitch)



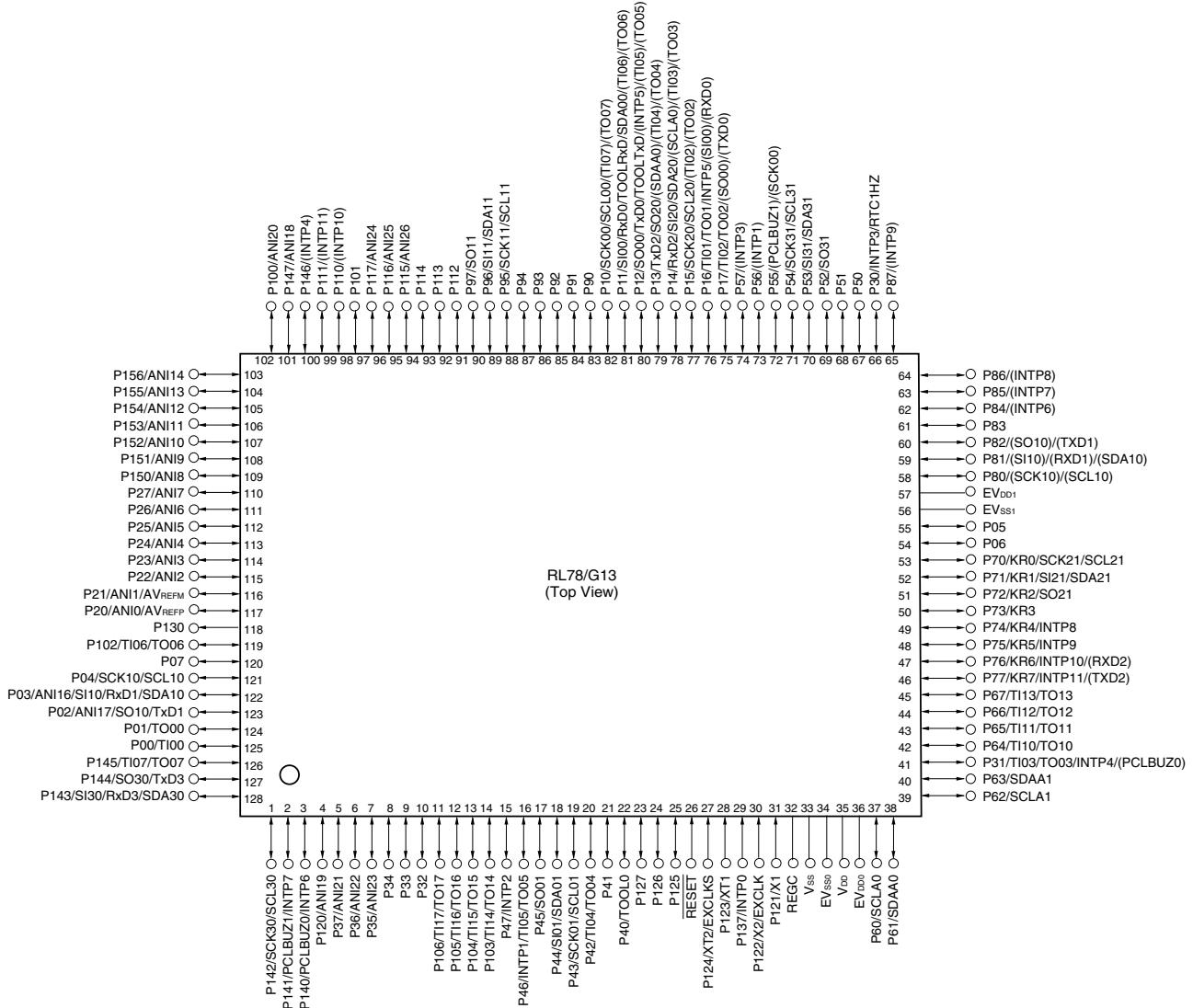
Caution Connect the REGC pin to V_{ss} via a capacitor (0.47 to 1 μ F).

Remarks 1. For pin identification, see **1.4 Pin Identification**.

2. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to **Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR)** in the RL78/G13 User's Manual.

1.3.14 128-pin products

- 128-pin plastic LFQFP (14 × 20 mm, 0.5 mm pitch)



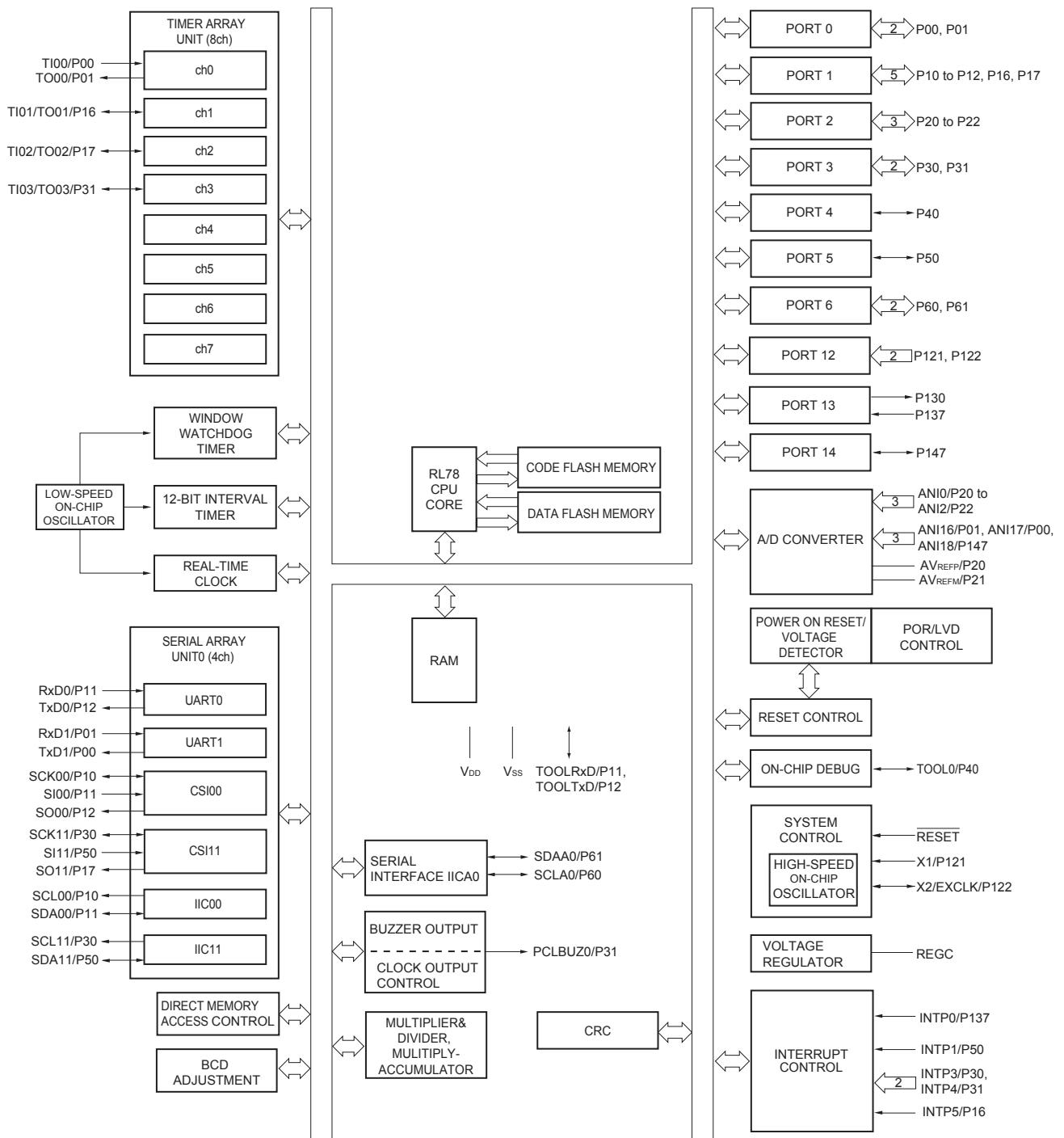
Cautions 1. Make EV_{SS0}, EV_{SS1} pins the same potential as Vss pin.

2. Make V_{DD} pin the potential that is higher than EV_{DD0}, EV_{DD1} pins (EV_{DD0} = EV_{DD1}).
3. Connect the REGC pin to Vss via a capacitor (0.47 to 1 μ F).

Remarks 1. For pin identification, see 1.4 Pin Identification.

2. When using the microcontroller for an application where the noise generated inside the microcontroller must be reduced, it is recommended to supply separate powers to the V_{DD}, EV_{DD0} and EV_{DD1} pins and connect the Vss, EV_{SS0} and EV_{SS1} pins to separate ground lines.
3. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR) in the RL78/G13 User's Manual.

1.5.3 25-pin products



($T_A = -40$ to $+85^\circ\text{C}$, $1.6 \text{ V} \leq EV_{DD0} = EV_{DD1} \leq V_{DD} \leq 5.5 \text{ V}$, $V_{SS} = EV_{SS0} = EV_{SS1} = 0 \text{ V}$) (5/5)

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit		
Input leakage current, high	I_{LIH1}	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P60 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P140 to P147		$V_I = EV_{DD0}$		1	μA		
	I_{LIH2}	P20 to P27, P137, P150 to P156, RESET		$V_I = V_{DD}$		1	μA		
	I_{LIH3}	P121 to P124 (X1, X2, XT1, XT2, EXCLK, EXCLKS)		$V_I = V_{DD}$	In input port or external clock input	1	μA		
						10	μA		
Input leakage current, low	I_{LIL1}	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P60 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P140 to P147		$V_I = EV_{SS0}$		-1	μA		
	I_{LIL2}	P20 to P27, P137, P150 to P156, RESET		$V_I = V_{SS}$		-1	μA		
	I_{LIL3}	P121 to P124 (X1, X2, XT1, XT2, EXCLK, EXCLKS)		$V_I = V_{SS}$	In input port or external clock input	-1	μA		
						-10	μA		
On-chip pll-up resistance	R_u	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P140 to P147		$V_I = EV_{SS0}$, In input port		10	20	100	$k\Omega$

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

Notes 1. Total current flowing into V_{DD} , EV_{DD0} , and EV_{DD1} , including the input leakage current flowing when the level of the input pin is fixed to V_{DD} , EV_{DD0} , and EV_{DD1} , or V_{SS} , EV_{SS0} , and EV_{SS1} . The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.

2. When high-speed on-chip oscillator and subsystem clock are stopped.
3. When high-speed system clock and subsystem clock are stopped.
4. When high-speed on-chip oscillator and high-speed system clock are stopped. When $AMPHS1 = 1$ (Ultra-low power consumption oscillation). However, not including the current flowing into the 12-bit interval timer and watchdog timer.
5. Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.

HS (high-speed main) mode: $2.7 \text{ V} \leq V_{DD} \leq 5.5 \text{ V}$ @ 1 MHz to 32 MHz

$2.4 \text{ V} \leq V_{DD} \leq 5.5 \text{ V}$ @ 1 MHz to 16 MHz

LS (low-speed main) mode: $1.8 \text{ V} \leq V_{DD} \leq 5.5 \text{ V}$ @ 1 MHz to 8 MHz

LV (low-voltage main) mode: $1.6 \text{ V} \leq V_{DD} \leq 5.5 \text{ V}$ @ 1 MHz to 4 MHz

- Remarks**
1. f_{MX} : High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
 2. f_{IH} : High-speed on-chip oscillator clock frequency
 3. f_{SUB} : Subsystem clock frequency (XT1 clock oscillation frequency)
 4. Except subsystem clock operation, temperature condition of the TYP. value is $T_A = 25^\circ\text{C}$

2.5 Peripheral Functions Characteristics

AC Timing Test Points



2.5.1 Serial array unit

(1) During communication at same potential (UART mode)

($T_A = -40$ to $+85^\circ\text{C}$, $1.6 \text{ V} \leq EV_{DD0} = EV_{DD1} \leq V_{DD} \leq 5.5 \text{ V}$, $V_{SS} = EV_{SS0} = EV_{SS1} = 0 \text{ V}$)

Parameter	Symbol	Conditions	HS (high-speed main) Mode	LS (low-speed main) Mode	LV (low-voltage main) Mode		Unit
			MIN.	MAX.	MIN.	MAX.	
Transfer rate ^{Note 1}		2.4 V $\leq EV_{DD0} \leq 5.5 \text{ V}$	$f_{MCK}/6$ Note 2		$f_{MCK}/6$		$f_{MCK}/6$ bps
		Theoretical value of the maximum transfer rate $f_{MCK} = f_{CLK}$ ^{Note 3}	5.3		1.3		0.6 Mbps
		1.8 V $\leq EV_{DD0} \leq 5.5 \text{ V}$	$f_{MCK}/6$ Note 2		$f_{MCK}/6$		$f_{MCK}/6$ bps
		Theoretical value of the maximum transfer rate $f_{MCK} = f_{CLK}$ ^{Note 3}	5.3		1.3		0.6 Mbps
		1.7 V $\leq EV_{DD0} \leq 5.5 \text{ V}$	$f_{MCK}/6$ Note 2		$f_{MCK}/6$ Note 2		$f_{MCK}/6$ bps
		Theoretical value of the maximum transfer rate $f_{MCK} = f_{CLK}$ ^{Note 3}	5.3		1.3		0.6 Mbps
		1.6 V $\leq EV_{DD0} \leq 5.5 \text{ V}$	—		$f_{MCK}/6$ Note 2		$f_{MCK}/6$ bps
		Theoretical value of the maximum transfer rate $f_{MCK} = f_{CLK}$ ^{Note 3}	—		1.3		0.6 Mbps

Notes 1. Transfer rate in the SNOOZE mode is 4800 bps only.

2. The following conditions are required for low voltage interface when $EV_{DD0} < V_{DD}$.

2.4 V $\leq EV_{DD0} < 2.7 \text{ V}$: MAX. 2.6 Mbps

1.8 V $\leq EV_{DD0} < 2.4 \text{ V}$: MAX. 1.3 Mbps

1.6 V $\leq EV_{DD0} < 1.8 \text{ V}$: MAX. 0.6 Mbps

3. The maximum operating frequencies of the CPU/peripheral hardware clock (f_{CLK}) are:

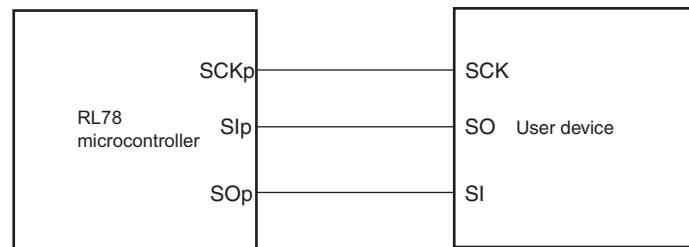
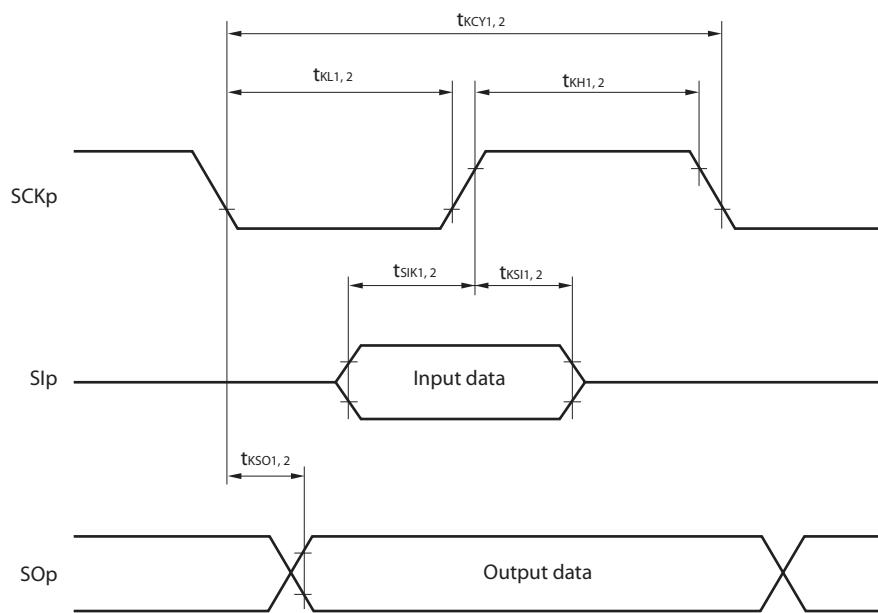
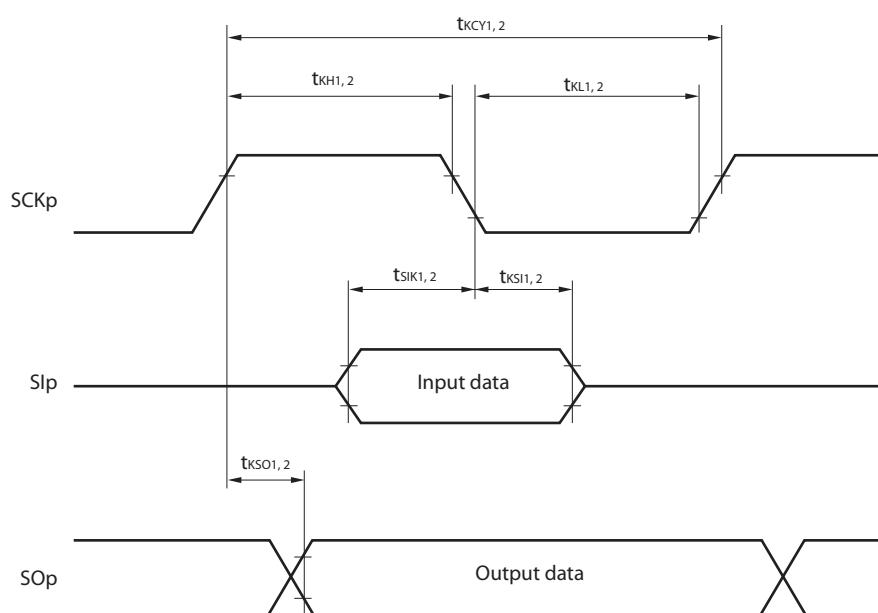
HS (high-speed main) mode: 32 MHz (2.7 V $\leq V_{DD} \leq 5.5 \text{ V}$)

16 MHz (2.4 V $\leq V_{DD} \leq 5.5 \text{ V}$)

LS (low-speed main) mode: 8 MHz (1.8 V $\leq V_{DD} \leq 5.5 \text{ V}$)

LV (low-voltage main) mode: 4 MHz (1.6 V $\leq V_{DD} \leq 5.5 \text{ V}$)

Caution Select the normal input buffer for the RxDq pin and the normal output mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg).

CSI mode connection diagram (during communication at same potential)**CSI mode serial transfer timing (during communication at same potential)**(When $\text{DAP}_{mn} = 0$ and $\text{CKP}_{mn} = 0$, or $\text{DAP}_{mn} = 1$ and $\text{CKP}_{mn} = 1$.)**CSI mode serial transfer timing (during communication at same potential)**(When $\text{DAP}_{mn} = 0$ and $\text{CKP}_{mn} = 1$, or $\text{DAP}_{mn} = 1$ and $\text{CKP}_{mn} = 0$.)

- Remarks**
1. p: CSI number ($p = 00, 01, 10, 11, 20, 21, 30, 31$)
 2. m: Unit number, n: Channel number ($mn = 00$ to 03 , 10 to 13)

(9) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (slave mode, SCKp... external clock input)

($T_A = -40$ to $+85^\circ\text{C}$, $1.8 \text{ V} \leq EV_{DD0} = EV_{DD1} \leq V_{DD} \leq 5.5 \text{ V}$, $V_{SS} = EV_{SS0} = EV_{SS1} = 0 \text{ V}$) (2/2)

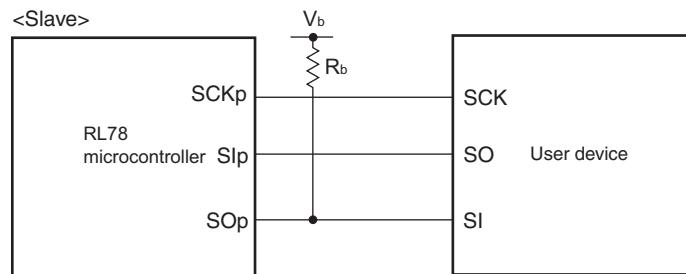
Parameter	Symbol	Conditions	HS (high-speed main) Mode		LS (low-speed main) Mode		LV (low-voltage main) Mode		Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp high-/low-level width	t_{KH2} , t_{KL2}	4.0 V $\leq EV_{DD0} \leq 5.5$ V, 2.7 V $\leq V_b \leq 4.0$ V	$t_{KCY2}/2$ – 12		$t_{KCY2}/2$ – 50		$t_{KCY2}/2$ – 50		ns
		2.7 V $\leq EV_{DD0} < 4.0$ V, 2.3 V $\leq V_b \leq 2.7$ V	$t_{KCY2}/2$ – 18		$t_{KCY2}/2$ – 50		$t_{KCY2}/2$ – 50		ns
		1.8 V $\leq EV_{DD0} < 3.3$ V, 1.6 V $\leq V_b \leq 2.0$ V ^{Note 2}	$t_{KCY2}/2$ – 50		$t_{KCY2}/2$ – 50		$t_{KCY2}/2$ – 50		ns
Slp setup time (to SCKp↑) ^{Note 3}	t_{SIK2}	4.0 V $\leq EV_{DD0} \leq 5.5$ V, 2.7 V $\leq V_b \leq 4.0$ V	$1/f_{MCK}$ + 20		$1/f_{MCK}$ + 30		$1/f_{MCK}$ + 30		ns
		2.7 V $\leq EV_{DD0} < 4.0$ V, 2.3 V $\leq V_b \leq 2.7$ V	$1/f_{MCK}$ + 20		$1/f_{MCK}$ + 30		$1/f_{MCK}$ + 30		ns
		1.8 V $\leq EV_{DD0} < 3.3$ V, 1.6 V $\leq V_b \leq 2.0$ V ^{Note 2}	$1/f_{MCK}$ + 30		$1/f_{MCK}$ + 30		$1/f_{MCK}$ + 30		ns
Slp hold time (from SCKp↑) ^{Note 4}	t_{SIS2}		$1/f_{MCK} +$ 31		$1/f_{MCK}$ + 31		$1/f_{MCK}$ + 31		ns
Delay time from SCKp↓ to SOp output ^{Note 5}	t_{KS02}	4.0 V $\leq EV_{DD0} \leq 5.5$ V, 2.7 V $\leq V_b \leq 4.0$ V, $C_b = 30 \text{ pF}$, $R_b = 1.4 \text{ k}\Omega$		$2/f_{MCK}$ + 120		$2/f_{MCK}$ + 573		$2/f_{MCK}$ + 573	ns
		2.7 V $\leq EV_{DD0} < 4.0$ V, 2.3 V $\leq V_b \leq 2.7$ V, $C_b = 30 \text{ pF}$, $R_b = 2.7 \text{ k}\Omega$		$2/f_{MCK}$ + 214		$2/f_{MCK}$ + 573		$2/f_{MCK}$ + 573	ns
		1.8 V $\leq EV_{DD0} < 3.3$ V, 1.6 V $\leq V_b \leq 2.0$ V ^{Note 2} , $C_b = 30 \text{ pF}$, $R_b = 5.5 \text{ k}\Omega$		$2/f_{MCK}$ + 573		$2/f_{MCK}$ + 573		$2/f_{MCK}$ + 573	ns

Notes 1. Transfer rate in the SNOOZE mode : MAX. 1 Mbps

2. Use it with $EV_{DD0} \geq V_b$.
3. When $DAP_{mn} = 0$ and $CKP_{mn} = 0$, or $DAP_{mn} = 1$ and $CKP_{mn} = 1$. The Slp setup time becomes “to SCKp↑” when $DAP_{mn} = 0$ and $CKP_{mn} = 1$, or $DAP_{mn} = 1$ and $CKP_{mn} = 0$.
4. When $DAP_{mn} = 0$ and $CKP_{mn} = 0$, or $DAP_{mn} = 1$ and $CKP_{mn} = 1$. The Slp hold time becomes “from SCKp↑” when $DAP_{mn} = 0$ and $CKP_{mn} = 1$, or $DAP_{mn} = 1$ and $CKP_{mn} = 0$.
5. When $DAP_{mn} = 0$ and $CKP_{mn} = 0$, or $DAP_{mn} = 1$ and $CKP_{mn} = 1$. The delay time to SOp output becomes “from SCKp↑” when $DAP_{mn} = 0$ and $CKP_{mn} = 1$, or $DAP_{mn} = 1$ and $CKP_{mn} = 0$.

Caution Select the TTL input buffer for the Slp pin and the N-ch open drain output (V_{DD} tolerance (for the 20- to 52-pin products)/ EV_{DD} tolerance (for the 64- to 128-pin products)) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL} , see the DC characteristics with TTL input buffer selected.

(Remarks are listed on the next page.)

CSI mode connection diagram (during communication at different potential)

- Remarks**
1. $R_b[\Omega]$: Communication line (SO_p) pull-up resistance, $C_b[F]$: Communication line (SO_p) load capacitance, $V_b[V]$: Communication line voltage
 2. p: CSI number (p = 00, 01, 10, 20, 30, 31), m: Unit number, n: Channel number (mn = 00, 01, 02, 10, 12, 13), g: PIM and POM number (g = 0, 1, 4, 5, 8, 14)
 3. fmck: Serial array unit operation clock frequency
(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn).
m: Unit number, n: Channel number (mn = 00, 01, 02, 10, 12, 13))
 4. CSI01 of 48-, 52-, 64-pin products, and CSI11 and CSI21 cannot communicate at different potential.
Use other CSI for communication at different potential.

- (3) When reference voltage (+) = V_{DD} ($\text{ADREFP1} = 0$, $\text{ADREFP0} = 0$), reference voltage (-) = V_{SS} ($\text{ADREFM} = 0$), target pin : ANI0 to ANI14, ANI16 to ANI26, internal reference voltage, and temperature sensor output voltage

($T_A = -40$ to $+85^\circ\text{C}$, $1.6 \text{ V} \leq EV_{DD0} = EV_{DD1} \leq V_{DD} \leq 5.5 \text{ V}$, $V_{SS} = EV_{SS0} = EV_{SS1} = 0 \text{ V}$, Reference voltage (+) = V_{DD} , Reference voltage (-) = V_{SS})

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error ^{Note 1}	AINL	10-bit resolution	1.8 V $\leq V_{DD} \leq 5.5 \text{ V}$		1.2	± 7.0	LSB
			1.6 V $\leq V_{DD} \leq 5.5 \text{ V}$ Note 3		1.2	± 10.5	LSB
Conversion time	t _{CONV}	10-bit resolution Target pin: ANI0 to ANI14, ANI16 to ANI26	3.6 V $\leq V_{DD} \leq 5.5 \text{ V}$	2.125		39	μs
			2.7 V $\leq V_{DD} \leq 5.5 \text{ V}$	3.1875		39	μs
			1.8 V $\leq V_{DD} \leq 5.5 \text{ V}$	17		39	μs
			1.6 V $\leq V_{DD} \leq 5.5 \text{ V}$	57		95	μs
Conversion time	t _{CONV}	10-bit resolution Target pin: Internal reference voltage, and temperature sensor output voltage (HS (high-speed main) mode)	3.6 V $\leq V_{DD} \leq 5.5 \text{ V}$	2.375		39	μs
			2.7 V $\leq V_{DD} \leq 5.5 \text{ V}$	3.5625		39	μs
			2.4 V $\leq V_{DD} \leq 5.5 \text{ V}$	17		39	μs
Zero-scale error ^{Notes 1, 2}	E _{ZS}	10-bit resolution	1.8 V $\leq V_{DD} \leq 5.5 \text{ V}$			± 0.60	%FSR
			1.6 V $\leq V_{DD} \leq 5.5 \text{ V}$ Note 3			± 0.85	%FSR
Full-scale error ^{Notes 1, 2}	E _{FS}	10-bit resolution	1.8 V $\leq V_{DD} \leq 5.5 \text{ V}$			± 0.60	%FSR
			1.6 V $\leq V_{DD} \leq 5.5 \text{ V}$ Note 3			± 0.85	%FSR
Integral linearity error ^{Note 1}	ILE	10-bit resolution	1.8 V $\leq V_{DD} \leq 5.5 \text{ V}$			± 4.0	LSB
			1.6 V $\leq V_{DD} \leq 5.5 \text{ V}$ Note 3			± 6.5	LSB
Differential linearity error ^{Note 1}	DLE	10-bit resolution	1.8 V $\leq V_{DD} \leq 5.5 \text{ V}$			± 2.0	LSB
			1.6 V $\leq V_{DD} \leq 5.5 \text{ V}$ Note 3			± 2.5	LSB
Analog input voltage	V _{AIN}	ANI0 to ANI14		0		V_{DD}	V
		ANI16 to ANI26		0		EV_{DD0}	V
		Internal reference voltage (2.4 V $\leq V_{DD} \leq 5.5 \text{ V}$, HS (high-speed main) mode)		V_{BGR} ^{Note 4}			V
		Temperature sensor output voltage (2.4 V $\leq V_{DD} \leq 5.5 \text{ V}$, HS (high-speed main) mode)		V_{TMPS25} ^{Note 4}			V

- Notes**
- Excludes quantization error ($\pm 1/2$ LSB).
 - This value is indicated as a ratio (%FSR) to the full-scale value.
 - When the conversion time is set to 57 μs (min.) and 95 μs (max.).
 - Refer to **2.6.2 Temperature sensor/internal reference voltage characteristics**.

2.6.5 Power supply voltage rising slope characteristics

($T_A = -40$ to $+85^\circ\text{C}$, $V_{SS} = 0$ V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Power supply voltage rising slope	S_{VDD}				54	V/ms

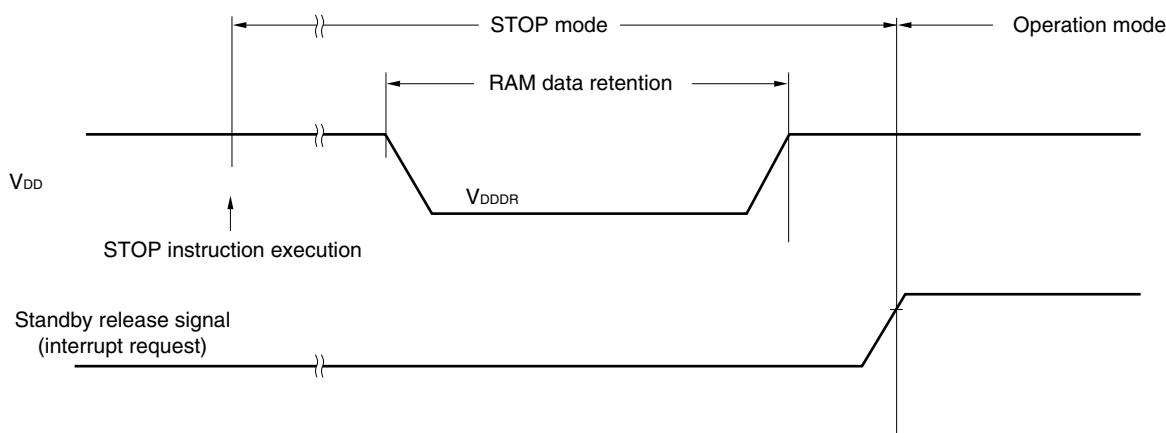
Caution Make sure to keep the internal reset state by the LVD circuit or an external reset until V_{DD} reaches the operating voltage range shown in 2.4 AC Characteristics.

2.7 RAM Data Retention Characteristics

($T_A = -40$ to $+85^\circ\text{C}$, $V_{SS} = 0$ V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Data retention supply voltage	V_{DDDR}		1.46 ^{Note}		5.5	V

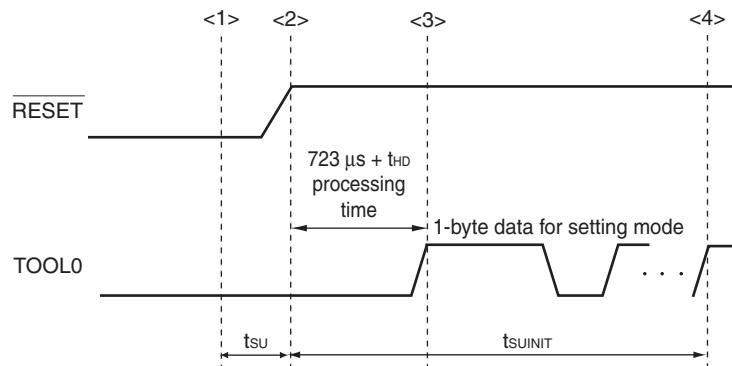
Note This depends on the POR detection voltage. For a falling voltage, data in RAM are retained until the voltage reaches the level that triggers a POR reset but not once it reaches the level at which a POR reset is generated.



2.10 Timing of Entry to Flash Memory Programming Modes

($T_A = -40$ to $+85^\circ\text{C}$, $1.8 \text{ V} \leq EV_{DD0} = EV_{DD1} \leq V_{DD} \leq 5.5 \text{ V}$, $V_{SS} = EV_{SS0} = EV_{SS1} = 0 \text{ V}$)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Time to complete the communication for the initial setting after the external reset is released	t_{SUINIT}	POR and LVD reset must be released before the external reset is released.			100	ms
Time to release the external reset after the TOOL0 pin is set to the low level	ts_u	POR and LVD reset must be released before the external reset is released.	10			μs
Time to hold the TOOL0 pin at the low level after the external reset is released (excluding the processing time of the firmware to control the flash memory)	t_{HD}	POR and LVD reset must be released before the external reset is released.	1			ms



- <1> The low level is input to the TOOL0 pin.
- <2> The external reset is released (POR and LVD reset must be released before the external reset is released.).
- <3> The TOOL0 pin is set to the high level.
- <4> Setting of the flash memory programming mode by UART reception and complete the baud rate setting.

Remark t_{SUINIT} : Communication for the initial setting must be completed within 100 ms after the external reset is released during this period.

ts_u : Time to release the external reset after the TOOL0 pin is set to the low level

t_{HD} : Time to hold the TOOL0 pin at the low level after the external reset is released (excluding the processing time of the firmware to control the flash memory)

(TA = -40 to +105°C, 2.4 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V) (4/5)

Items	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Output voltage, high	V _{OH1}	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P130, P140 to P147	4.0 V ≤ EV _{DD0} ≤ 5.5 V, I _{OH1} = -3.0 mA	EV _{DD0} – 0.7		V
			2.7 V ≤ EV _{DD0} ≤ 5.5 V, I _{OH1} = -2.0 mA	EV _{DD0} – 0.6		V
			2.4 V ≤ EV _{DD0} ≤ 5.5 V, I _{OH1} = -1.5 mA	EV _{DD0} – 0.5		V
	V _{OH2}	P20 to P27, P150 to P156	2.4 V ≤ V _{DD} ≤ 5.5 V, I _{OH2} = -100 μA	V _{DD} – 0.5		V
Output voltage, low	V _{OL1}	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P130, P140 to P147	4.0 V ≤ EV _{DD0} ≤ 5.5 V, I _{OL1} = 8.5 mA		0.7	V
			4.0 V ≤ EV _{DD0} ≤ 5.5 V, I _{OL1} = 3.0 mA		0.6	V
			2.7 V ≤ EV _{DD0} ≤ 5.5 V, I _{OL1} = 1.5 mA		0.4	V
			2.4 V ≤ EV _{DD0} ≤ 5.5 V, I _{OL1} = 0.6 mA		0.4	V
	V _{OL2}	P20 to P27, P150 to P156	2.4 V ≤ V _{DD} ≤ 5.5 V, I _{OL2} = 400 μA		0.4	V
	V _{OL3}	P60 to P63	4.0 V ≤ EV _{DD0} ≤ 5.5 V, I _{OL3} = 15.0 mA		2.0	V
			4.0 V ≤ EV _{DD0} ≤ 5.5 V, I _{OL3} = 5.0 mA		0.4	V
			2.7 V ≤ EV _{DD0} ≤ 5.5 V, I _{OL3} = 3.0 mA		0.4	V
			2.4 V ≤ EV _{DD0} ≤ 5.5 V, I _{OL3} = 2.0 mA		0.4	V

Caution P00, P02 to P04, P10 to P15, P17, P43 to P45, P50, P52 to P55, P71, P74, P80 to P82, P96, and P142 to P144 do not output high level in N-ch open-drain mode.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

(4) During communication at same potential (simplified I²C mode)(TA = -40 to +105°C, 2.4 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V)

Parameter	Symbol	Conditions	HS (high-speed main) Mode		Unit
			MIN.	MAX.	
SCL _r clock frequency	f _{SCL}	2.7 V ≤ EV _{DD0} ≤ 5.5 V, C _b = 50 pF, R _b = 2.7 kΩ		400 ^{Note1}	kHz
		2.4 V ≤ EV _{DD0} ≤ 5.5 V, C _b = 100 pF, R _b = 3 kΩ		100 ^{Note1}	kHz
Hold time when SCL _r = "L"	t _{LOW}	2.7 V ≤ EV _{DD0} ≤ 5.5 V, C _b = 50 pF, R _b = 2.7 kΩ	1200		ns
		2.4 V ≤ EV _{DD0} ≤ 5.5 V, C _b = 100 pF, R _b = 3 kΩ	4600		ns
Hold time when SCL _r = "H"	t _{HIGH}	2.7 V ≤ EV _{DD0} ≤ 5.5 V, C _b = 50 pF, R _b = 2.7 kΩ	1200		ns
		2.4 V ≤ EV _{DD0} ≤ 5.5 V, C _b = 100 pF, R _b = 3 kΩ	4600		ns
Data setup time (reception)	t _{SU:DAT}	2.7 V ≤ EV _{DD0} ≤ 5.5 V, C _b = 50 pF, R _b = 2.7 kΩ	1/f _{MCK} + 220 ^{Note2}		ns
		2.4 V ≤ EV _{DD} ≤ 5.5 V, C _b = 100 pF, R _b = 3 kΩ	1/f _{MCK} + 580 ^{Note2}		ns
Data hold time (transmission)	t _{HD:DAT}	2.7 V ≤ EV _{DD0} ≤ 5.5 V, C _b = 50 pF, R _b = 2.7 kΩ	0	770	ns
		2.4 V ≤ EV _{DD0} ≤ 5.5 V, C _b = 100 pF, R _b = 3 kΩ	0	1420	ns

Notes 1. The value must also be equal to or less than f_{MCK}/4.2. Set the f_{MCK} value to keep the hold time of SCL_r = "L" and SCL_r = "H".**Caution** Select the normal input buffer and the N-ch open drain output (V_{DD} tolerance (for the 20- to 52-pin products)/EV_{DD} tolerance (for the 64- to 100-pin products)) mode for the SDAr pin and the normal output mode for the SCL_r pin by using port input mode register g (PIMg) and port output mode register h (POMh).

(Remarks are listed on the next page.)

5. The smaller maximum transfer rate derived by using $f_{MCK}/12$ or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when $2.4 \text{ V} \leq EV_{DD0} < 3.3 \text{ V}$ and $1.6 \text{ V} \leq V_b \leq 2.0 \text{ V}$

$$\text{Maximum transfer rate} = \frac{1}{\{-C_b \times R_b \times \ln(1 - \frac{1.5}{V_b})\} \times 3} \text{ [bps]}$$

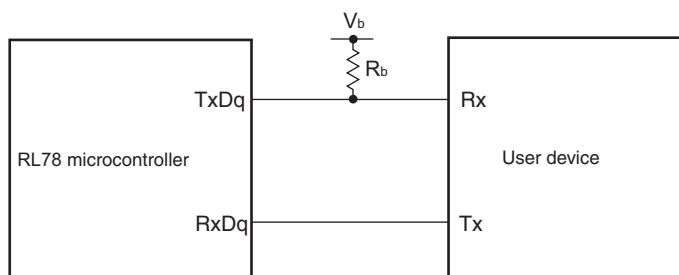
$$\text{Baud rate error (theoretical value)} = \frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln(1 - \frac{1.5}{V_b})\}}{\left(\frac{1}{\text{Transfer rate}}\right) \times \text{Number of transferred bits}} \times 100 \text{ [%]}$$

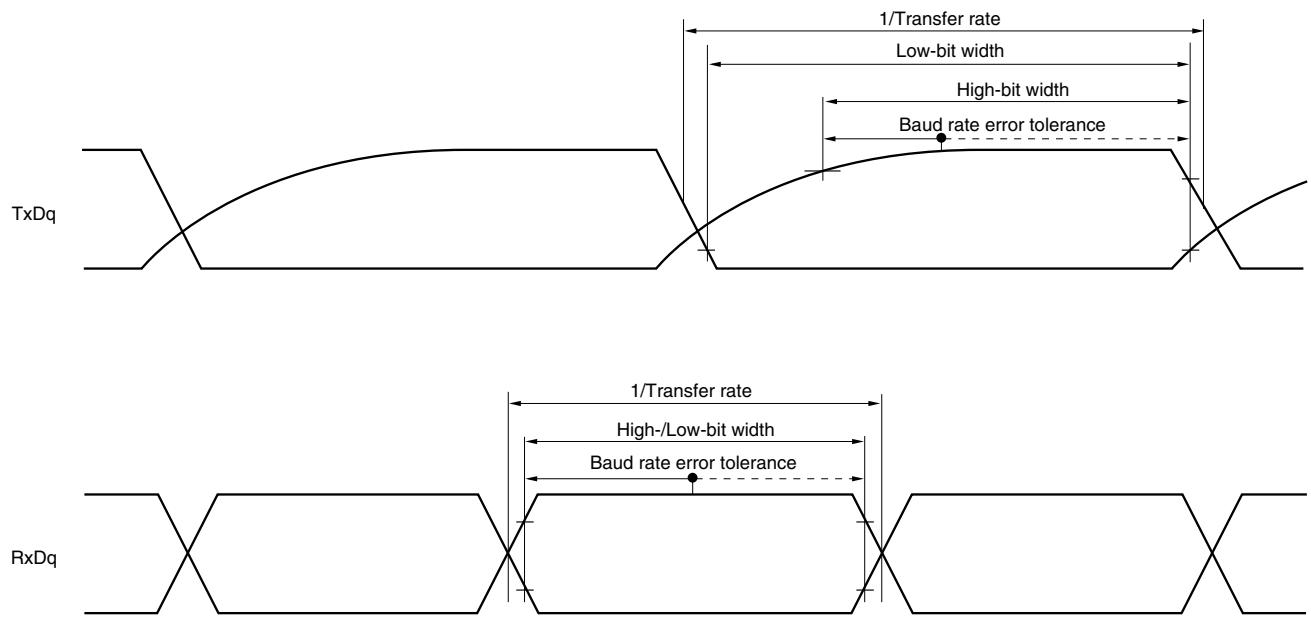
* This value is the theoretical value of the relative difference between the transmission and reception sides.

6. This value as an example is calculated when the conditions described in the “Conditions” column are met. Refer to Note 5 above to calculate the maximum transfer rate under conditions of the customer.

Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (V_{DD} tolerance (for the 20- to 52-pin products)/ EV_{DD} tolerance (for the 64- to 100-pin products)) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL} , see the DC characteristics with TTL input buffer selected.

UART mode connection diagram (during communication at different potential)



UART mode bit width (during communication at different potential) (reference)

- Remarks**
1. $R_b[\Omega]$: Communication line (TxDq) pull-up resistance,
 $C_b[F]$: Communication line (TxDq) load capacitance, $V_b[V]$: Communication line voltage
 2. q: UART number (q = 0 to 3), g: PIM and POM number (g = 0, 1, 8, 14)
 3. f_{MCK} : Serial array unit operation clock frequency
 (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn).
 m: Unit number, n: Channel number (mn = 00 to 03, 10 to 13))
 4. UART2 cannot communicate at different potential when bit 1 (PIOR1) of peripheral I/O redirection register (PIOR) is 1.

(4) When reference voltage (+) = Internal reference voltage (ADREFP1 = 1, ADREFP0 = 0), reference voltage (-) = AV_{REFM}/ANI1 (ADREFM = 1), target pin : ANI0, ANI2 to ANI14, ANI16 to ANI26

(TA = -40 to +105°C, 2.4 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V, Reference voltage (+) = V_{BGR}^{Note 3}, Reference voltage (-) = AV_{REFM}^{Note 4} = 0 V, HS (high-speed main) mode)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Resolution	RES			8		bit	
Conversion time	t _{CONV}	8-bit resolution	2.4 V ≤ V _{DD} ≤ 5.5 V	17		39	μs
Zero-scale error ^{Notes 1, 2}	E _{Zs}	8-bit resolution	2.4 V ≤ V _{DD} ≤ 5.5 V			±0.60	%FSR
Integral linearity error ^{Note 1}	ILE	8-bit resolution	2.4 V ≤ V _{DD} ≤ 5.5 V			±2.0	LSB
Differential linearity error ^{Note 1}	DLE	8-bit resolution	2.4 V ≤ V _{DD} ≤ 5.5 V			±1.0	LSB
Analog input voltage	V _{AIN}			0		V _{BGR} ^{Note 3}	V

Notes 1. Excludes quantization error (±1/2 LSB).

2. This value is indicated as a ratio (%FSR) to the full-scale value.

3. Refer to 3.6.2 Temperature sensor/internal reference voltage characteristics.

4. When reference voltage (-) = V_{SS}, the MAX. values are as follows.

Zero-scale error: Add ±0.35%FSR to the MAX. value when reference voltage (-) = AV_{REFM}.

Integral linearity error: Add ±0.5 LSB to the MAX. value when reference voltage (-) = AV_{REFM}.

Differential linearity error: Add ±0.2 LSB to the MAX. value when reference voltage (-) = AV_{REFM}.

3.6.2 Temperature sensor/internal reference voltage characteristics

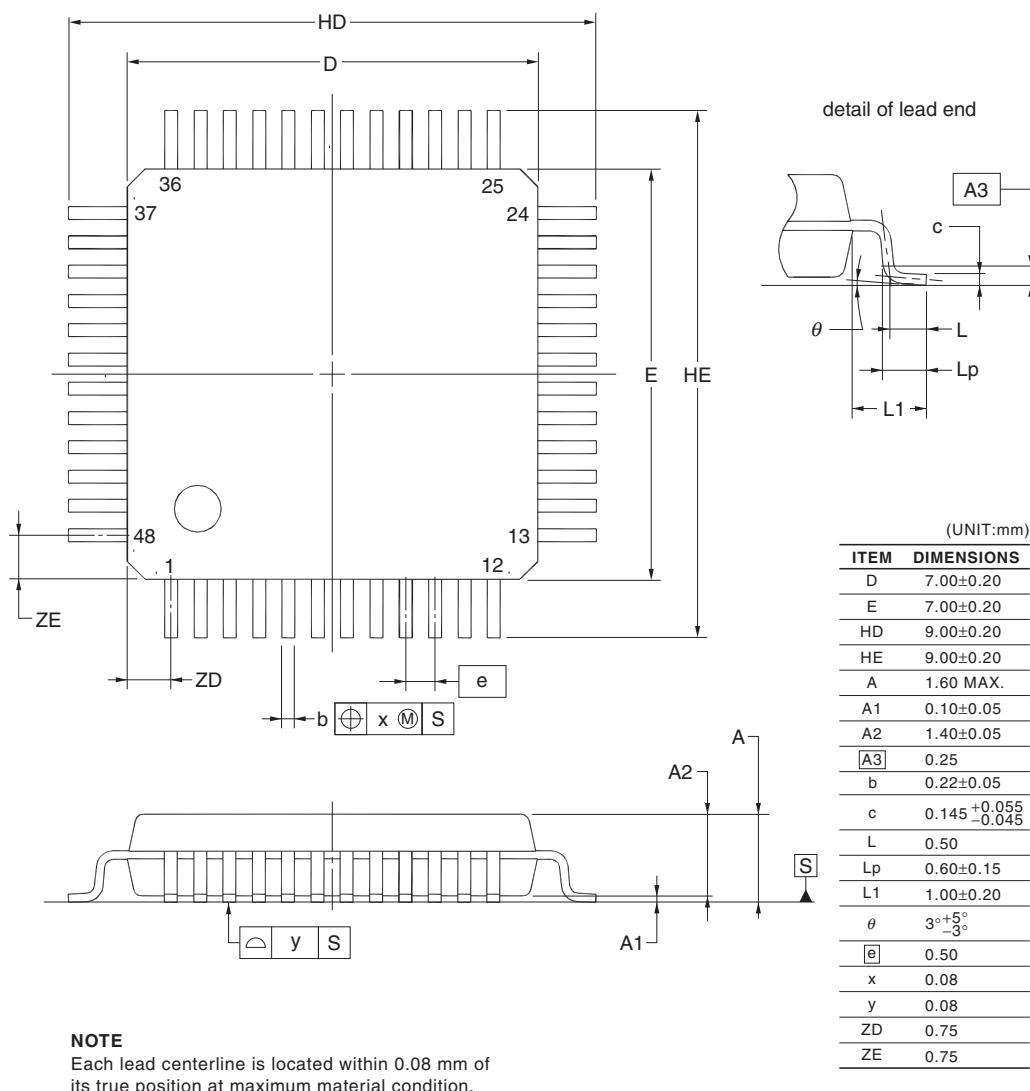
(TA = -40 to +105°C, 2.4 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V, HS (high-speed main) mode)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Temperature sensor output voltage	V _{TMP25}	Setting ADS register = 80H, TA = +25°C		1.05		V
Internal reference voltage	V _{BGR}	Setting ADS register = 81H	1.38	1.45	1.5	V
Temperature coefficient	F _{VTMP5}	Temperature sensor that depends on the temperature		-3.6		mV/°C
Operation stabilization wait time	t _{AMP}		5			μs

4.9 48-pin Products

R5F100GAAFB, R5F100GCAFB, R5F100GDAFB, R5F100GEAFB, R5F100GFAFB, R5F100GGAFB,
 R5F100GHAFB, R5F100GJAFB, R5F100GKAFB, R5F100GLAFB
 R5F101GAAFB, R5F101GCAFB, R5F101GDAFB, R5F101GEAFB, R5F101GFAFB, R5F101GGAFB,
 R5F101GHAFB, R5F101GJAFB, R5F101GKAFB, R5F101GLAFB
 R5F100GADFB, R5F100GCDFB, R5F100GDDFB, R5F100GEDFB, R5F100GFDFB, R5F100GGDFB,
 R5F100GHDDB, R5F100GJDFB, R5F100GKDFB, R5F100GLDFB
 R5F101GADFB, R5F101GCDFB, R5F101GDDFB, R5F101GEDFB, R5F101GFDFB, R5F101GGDFB,
 R5F101GHDDB, R5F101GJDFB, R5F101GKDFB, R5F101GLDFB
 R5F100GAGFB, R5F100GCGFB, R5F100GDGFB, R5F100GEGFB, R5F100GFGFB, R5F100GGGFB,
 R5F100GHGFB, R5F100GJGFB

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LFQFP48-7x7-0.50	PLQP0048KF-A	P48GA-50-8EU-1	0.16



4.11 64-pin Products

R5F100LCAFA, R5F100LDAFA, R5F100LEAFA, R5F100LFAFA, R5F100LGAFA, R5F100LHAFA, R5F100LJAFA,
 R5F100LKAFA, R5F100LLAFA
 R5F101LCAFA, R5F101LDAFA, R5F101LEAFA, R5F101LFAFA, R5F101LGAFA, R5F101LHAFA, R5F101LJAFA,
 R5F101LKAFA, R5F101LLAFA
 R5F100LCDFA, R5F100LDDFA, R5F100LEDFA, R5F100LF DFA, R5F100LG DFA, R5F100LHDFA, R5F100LJDFA,
 R5F100LK DFA, R5F100LL DFA
 R5F101LCDFA, R5F101LDDFA, R5F101LEDFA, R5F101LF DFA, R5F101LG DFA, R5F101LHDFA, R5F101LJDFA,
 R5F101LK DFA, R5F101LL DFA
 R5F100LCGFA, R5F100LDGFA, R5F100LEGFA, R5F100LFGFA, R5F100LGGFA, R5F100LHGFA,
 R5F100LJGFA

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LQFP64-12x12-0.65	PLQP0064JA-A	P64GK-65-UET-2	0.51

